

In re: Kong et al.  
Serial No.: 09/715,576  
Filed: November 17, 2000  
Page 2

B1  
sidewalls 51 makes it somewhat easier to retain the wafers in the pockets 52 during chemical vapor deposition, and also helps provide proper flow pattern for the CVD gases.

---

Please delete the paragraph beginning at page 10, line 23 of the Specification and replace it with the following paragraph.

---

B2  
A second cylinder broadly designated at 57 surrounds the first cylinder 54 and defines an annular space A between the first and second cylinders. The second cylinder 57 is likewise made of a material that is thermally responsive to the selected frequencies of electromagnetic radiation, and the annular space between the first and second cylinders (54, 57) is sufficiently large to permit the flow of gases therebetween for epitaxial growth on substrates in the wafer pockets 56, while small enough for the second cylinder 57 to heat the exposed face of substrates to substantially the same temperature as the first cylinder 54 heats the faces of substrates that are in direct contact with the first cylinder (i.e., the second cylinder directly or actively heats the substrate and first cylinder in response to electromagnetic radiation).

---

In the Claims:

Please cancel Claims 4 - ~~23~~<sup>§</sup>; 25 - 28 and 42 - 48.

Please amend Claim 1 as follows:

---

- B3  
sub 37
1. (Amended) A susceptor for minimizing or eliminating thermal gradients that affect a substrate wafer during epitaxial growth, said susceptor comprising:  
a first susceptor portion formed from graphite coated with silicon carbide and including a surface for receiving a semiconductor substrate wafer thereon; and